

Vishay Siliconix

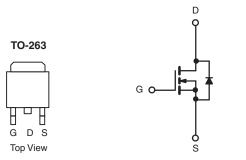
AUTOMOTIVE

COMPLIANT HALOGEN

FREE

# Automotive N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V <sub>DS</sub> (V)	150		
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.019		
I <sub>D</sub> (A)	85		
Configuration	Single		



N-Channel MOSFET

### **FEATURES**

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualifiedd



ORDERING INFORMATION	
Package	TO-263
Lead (Pb)-free and Halogen-free	SQM85N15-19-GE3

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		$V_{DS}$	150	V	
Gate-Source Voltage		$V_{GS}$	± 20		
Continuous Drain Current	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	85		
	T <sub>C</sub> = 125 °C		50		
Continuous Source Current (Diode Conduction) <sup>a</sup>		Is	120	А	
Pulsed Drain Currentb		I <sub>DM</sub>	140		
Single Pulse Avalanche Energy	L = 0.1 mH	I <sub>AS</sub>	52		
Single Pulse Avalanche Current	L = U. I IIII	E <sub>AS</sub>	135	mJ	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	- P <sub>D</sub>	375	W	
	T <sub>C</sub> = 125 °C		125		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount <sup>c</sup>	$R_{thJA}$	40	°C/W	
Junction-to-Case (Drain)		$R_{thJC}$	0.4	C/VV	

### Notes

- a. Package limited.
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.
- c. When mounted on 1" square P.C.B. (Fr-4 material).
- d. Parametric verification ongoing.

# SQM85N15-19

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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		1						
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		150	-	-	V	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		2.5	3.0	3.5	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA	
Zero Gate Voltage Drain Current		$V_{GS} = 0 V$	V <sub>DS</sub> = 150 V	-	-	1.0		
	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 150 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 150 V, T <sub>J</sub> = 175 °C	-	-	300		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	120	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A	-	0.016	0.019	Ω	
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 125 °C	-	-	0.039		
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 30 A, T <sub>J</sub> = 175 °C	-	-	0.051		
Forward Transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 30 A		-	79	-	S	
Dynamic <sup>b</sup>								
Input Capacitance	C <sub>iss</sub>		V <sub>DS</sub> = 25 V, f = 1 MHz	-	5026	6285	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	450	565		
Reverse Transfer Capacitance	C <sub>rss</sub>			-	165	205		
Total Gate Charge <sup>c</sup>	Qg		0 V V <sub>DS</sub> = 75 V, I <sub>D</sub> = 85 A	-	80	120	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = 10 V		-	33	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			-	12	-		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = 75 \text{ V}, \text{ R}_L = 0.88 \ \Omega$ $I_D \cong 85 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \ \Omega$		-	17	26	ns ns	
Rise Time <sup>c</sup>	t <sub>r</sub>			-	24	36		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	35	53		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	11	17		
Source-Drain Diode Ratings and Char-	acteristics <sup>b</sup>	•						
Pulsed Current <sup>a</sup>	I <sub>SM</sub>			-	-	140	Α	
Forward Voltage	$V_{SD}$	I <sub>F</sub> = 85 A, V <sub>GS</sub> = 0 V		_	0.9	1.5	V	

### Notes

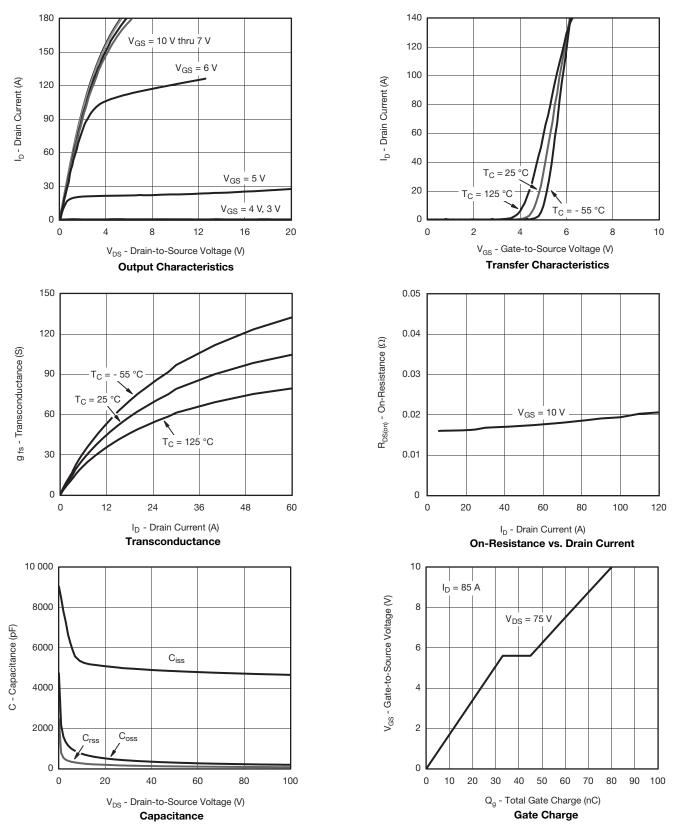
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





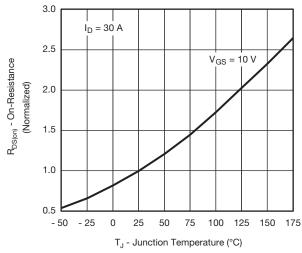
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)

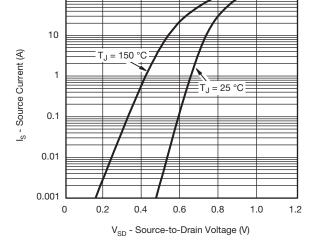


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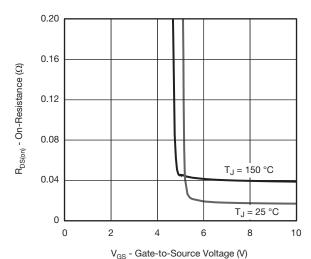


# **TYPICAL CHARACTERISTICS** ( $T_A = 25 \, ^{\circ}C$ , unless otherwise noted)

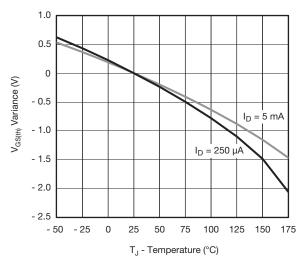






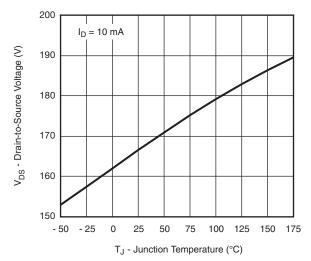


**Source Drain Diode Forward Voltage** 





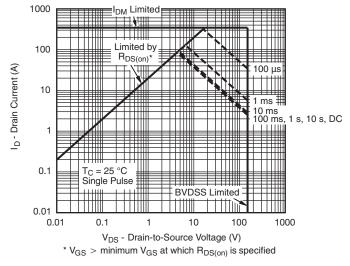




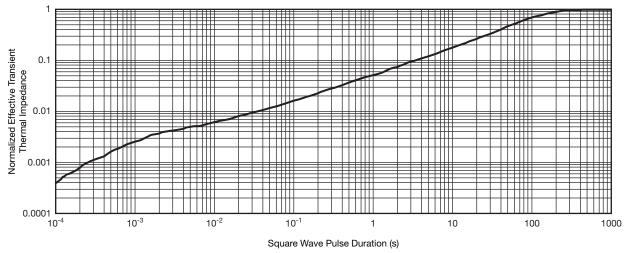
Drain Source Breakdown vs. Junction Temperature



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Safe Operating Area

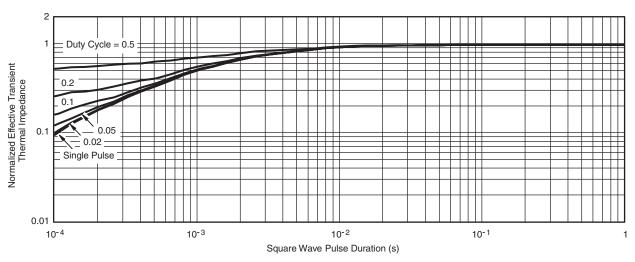


Normalized Thermal Transient Impedance, Junction-to-Ambient

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### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



### Normalized Thermal Transient Impedance, Junction-to-Case

### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction to Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction to Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg268668">www.vishay.com/ppg268668</a>.

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